

# MUN5111DW1T1 Series

Preferred Devices

## Dual Bias Resistor Transistors

### PNP Silicon Surface Mount Transistors with Monolithic Bias Resistor Network

The BRT (Bias Resistor Transistor) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. These digital transistors are designed to replace a single device and its external resistor bias network. The BRT eliminates these individual components by integrating them into a single device. In the MUN5111DW1T1 series, two BRT devices are housed in the SOT-363 package which is ideal for low-power surface mount applications where board space is at a premium.

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- Available in 8 mm, 7 inch/3000 Unit Tape and Reel

#### MAXIMUM RATINGS

( $T_A = 25^\circ\text{C}$  unless otherwise noted, common for  $Q_1$  and  $Q_2$ )

Rating	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-50	Vdc
Collector-Emitter Voltage	$V_{CEO}$	-50	Vdc
Collector Current	$I_C$	-100	mAdc

#### THERMAL CHARACTERISTICS

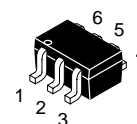
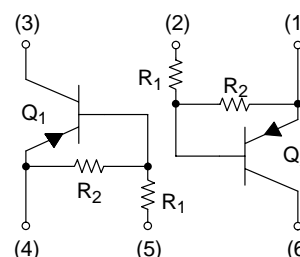
Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	187 (Note 1.) 256 (Note 2.)	mW
		1.5 (Note 1.) 2.0 (Note 2.)	mW/ $^\circ\text{C}$
Thermal Resistance – Junction-to-Ambient	$R_{\theta JA}$	670 (Note 1.) 490 (Note 2.)	$^\circ\text{C}/\text{W}$
Characteristic (Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	250 (Note 1.) 385 (Note 2.)	mW
		2.0 (Note 1.) 3.0 (Note 2.)	mW/ $^\circ\text{C}$
Thermal Resistance – Junction-to-Ambient	$R_{\theta JA}$	493 (Note 1.) 325 (Note 2.)	$^\circ\text{C}/\text{W}$
Thermal Resistance – Junction-to-Lead	$R_{\theta JL}$	188 (Note 1.) 208 (Note 2.)	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

1. FR-4 @ Minimum Pad
2. FR-4 @ 1.0 x 1.0 inch Pad



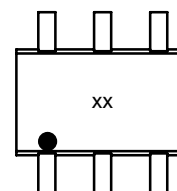
ON Semiconductor™

<http://onsemi.com>



SOT-363  
CASE 419B  
STYLE 1

#### MARKING DIAGRAM



xx = Device Marking  
(See Page 2)

#### DEVICE MARKING INFORMATION

See specific marking information in the device marking table on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

# MUN5111DW1T1 Series

## DEVICE MARKING AND RESISTOR VALUES

Device	Package	Marking	R1 (K)	R2 (K)	Shipping
MUN5111DW1T1	SOT-363	0A	10	10	3000/Tape & Reel
MUN5112DW1T1	SOT-363	0B	22	22	3000/Tape & Reel
MUN5113DW1T1	SOT-363	0C	47	47	3000/Tape & Reel
MUN5114DW1T1	SOT-363	0D	10	47	3000/Tape & Reel
MUN5115DW1T1 (Note 3.)	SOT-363	0E	10	∞	3000/Tape & Reel
MUN5116DW1T1 (Note 3.)	SOT-363	0F	4.7	∞	3000/Tape & Reel
MUN5130DW1T1 (Note 3.)	SOT-363	0G	1.0	1.0	3000/Tape & Reel
MUN5131DW1T1 (Note 3.)	SOT-363	0H	2.2	2.2	3000/Tape & Reel
MUN5132DW1T1 (Note 3.)	SOT-363	0J	4.7	4.7	3000/Tape & Reel
MUN5133DW1T1 (Note 3.)	SOT-363	0K	4.7	47	3000/Tape & Reel
MUN5134DW1T1 (Note 3.)	SOT-363	0L	22	47	3000/Tape & Reel
MUN5135DW1T1 (Note 3.)	SOT-363	0M	2.2	47	3000/Tape & Reel
MUN5136DW1T1 (Note 3.)	SOT-363	0N	100	100	3000/Tape & Reel
MUN5137DW1T1 (Note 3.)	SOT-363	0P	47	22	3000/Tape & Reel

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted, common for Q<sub>1</sub> and Q<sub>2</sub>)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

### OFF CHARACTERISTICS

Collector-Base Cutoff Current (V <sub>CB</sub> = -50 V, I <sub>E</sub> = 0)	I <sub>CBO</sub>	-	-	-100	nAdc
Collector-Emitter Cutoff Current (V <sub>CE</sub> = -50 V, I <sub>B</sub> = 0)	I <sub>CEO</sub>	-	-	-500	nAdc
Emitter-Base Cutoff Current (V <sub>EB</sub> = -6.0 V, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	-	-0.5	mAdc
	MUN5111DW1T1	-	-	-0.2	
	MUN5112DW1T1	-	-	-0.1	
	MUN5113DW1T1	-	-	-0.2	
	MUN5114DW1T1	-	-	-0.9	
	MUN5115DW1T1	-	-	-1.9	
	MUN5116DW1T1	-	-	-4.3	
	MUN5130DW1T1	-	-	-2.3	
	MUN5131DW1T1	-	-	-1.5	
	MUN5132DW1T1	-	-	-0.18	
	MUN5133DW1T1	-	-	-0.13	
	MUN5134DW1T1	-	-	-0.2	
	MUN5135DW1T1	-	-	-0.05	
	MUN5136DW1T1	-	-	-0.13	
	MUN5137DW1T1	-	-	-	
Collector-Base Breakdown Voltage (I <sub>C</sub> = -10 μA, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	-50	-	-	Vdc
Collector-Emitter Breakdown Voltage (Note 4.) (I <sub>C</sub> = -2.0 mA, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	-50	-	-	Vdc

### ON CHARACTERISTICS (Note 4.)

Collector-Emitter Saturation Voltage (I <sub>C</sub> = -10 mA, I <sub>E</sub> = -0.3 mA) (I <sub>C</sub> = -10 mA, I <sub>B</sub> = -5 mA) MUN5130DW1T1/MUN5131DW1T1 (I <sub>C</sub> = -10 mA, I <sub>B</sub> = -1 mA) MUN5115DW1T1/MUN5116DW1T1 MUN5132DW1T1/MUN5133DW1T1/MUN5134DW1T1	V <sub>CE(sat)</sub>	-	-	-0.25	Vdc
--	----------------------	---	---	-------	-----

3. New resistor combinations. Updated curves to follow in subsequent data sheets.

4. Pulse Test: Pulse Width < 300 μs, Duty Cycle < 2.0%



# MUN5111DW1T1 Series

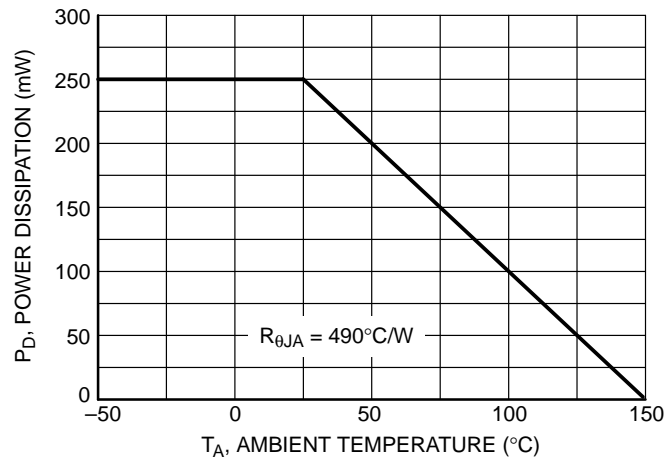


Figure 1. Derating Curve

# MUN5111DW1T1 Series

## TYPICAL ELECTRICAL CHARACTERISTICS — MUN5111DW1T1

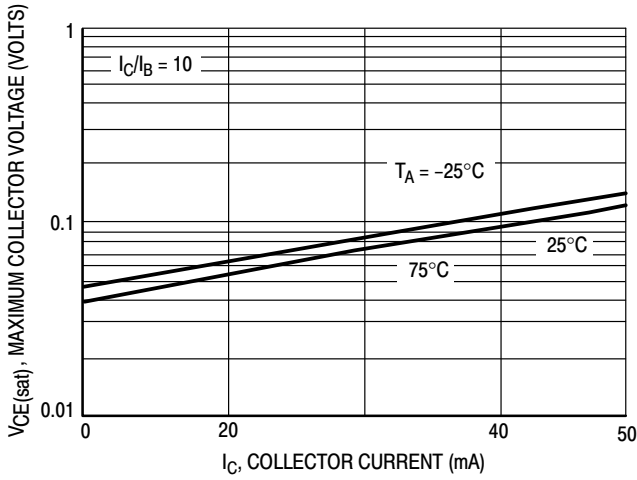


Figure 2.  $V_{CE(sat)}$  versus  $I_C$

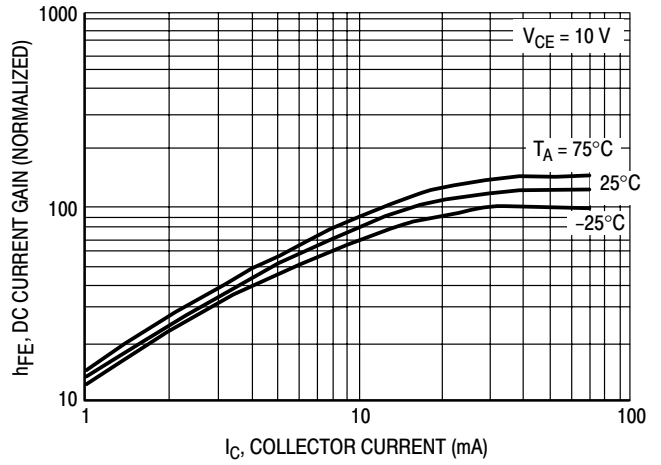


Figure 3. DC Current Gain

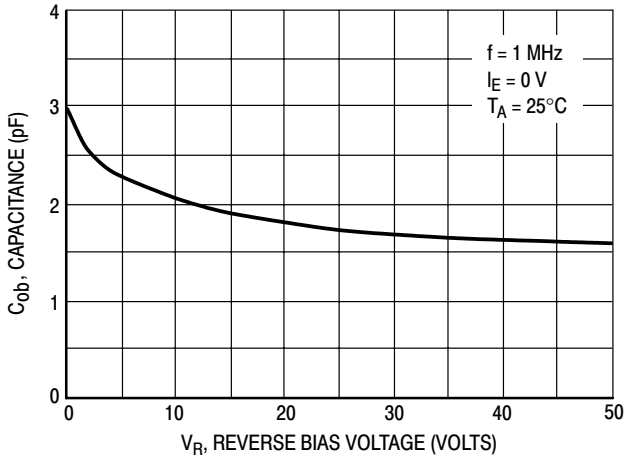


Figure 4. Output Capacitance

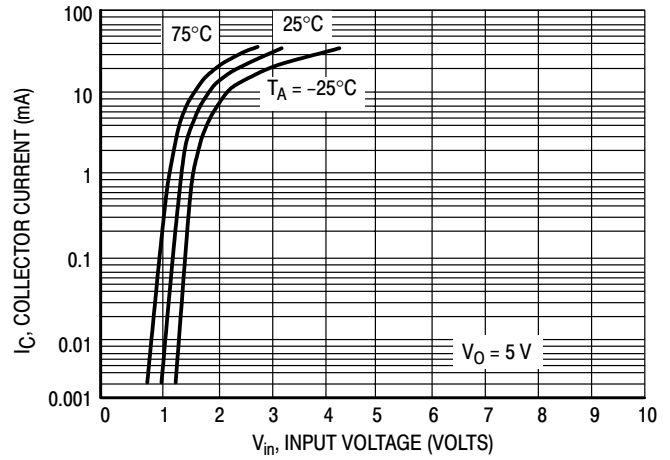


Figure 5. Output Current versus Input Voltage

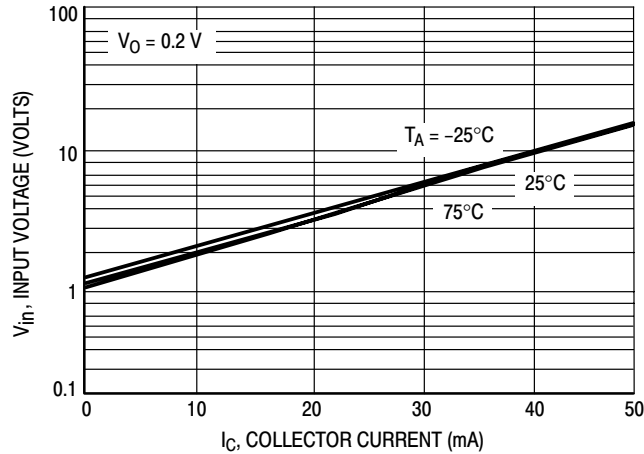


Figure 6. Input Voltage versus Output Current

# MUN5111DW1T1 Series

## TYPICAL ELECTRICAL CHARACTERISTICS — MUN5112DW1T1

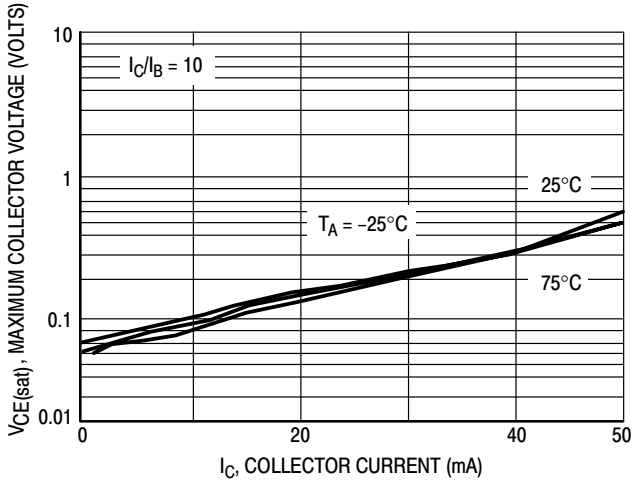


Figure 7.  $V_{CE(sat)}$  versus  $I_C$

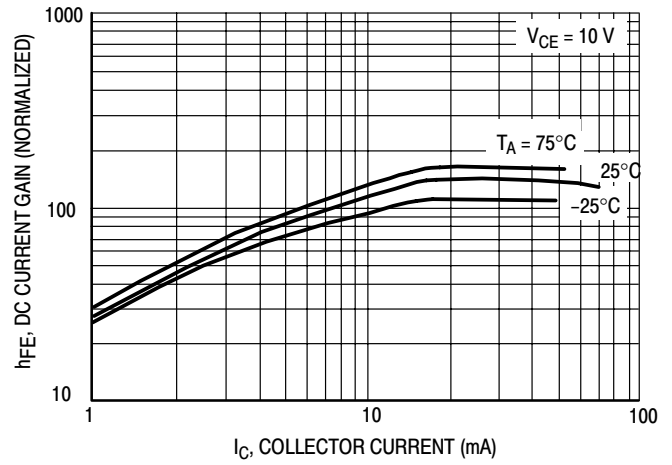


Figure 8. DC Current Gain

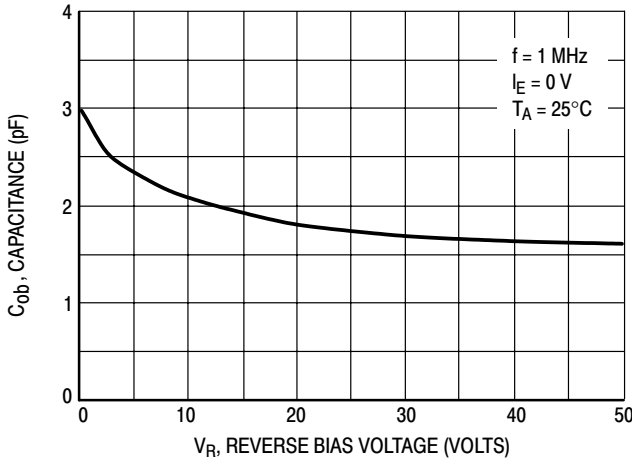


Figure 9. Output Capacitance

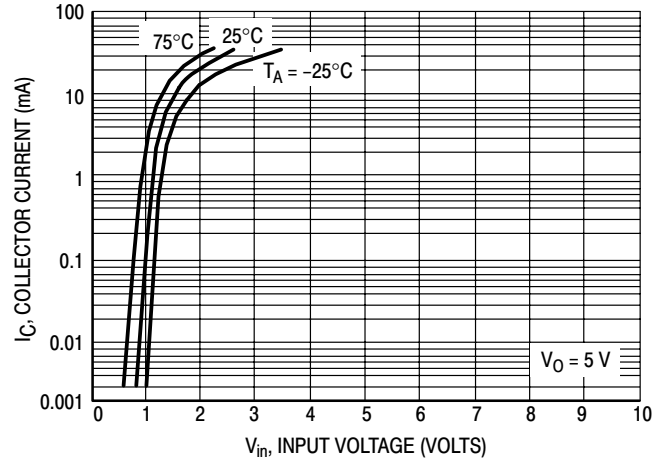


Figure 10. Output Current versus Input Voltage

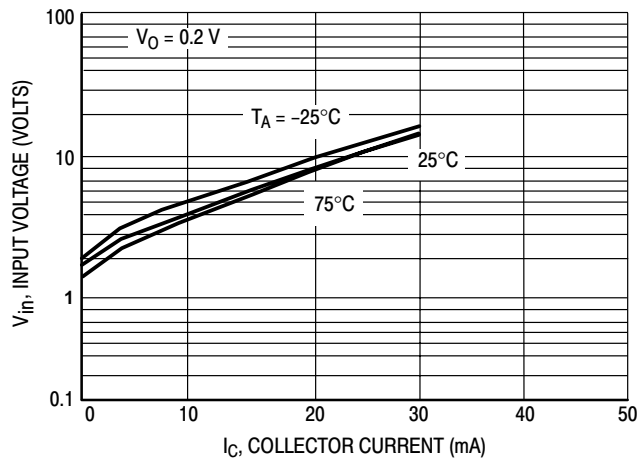


Figure 11. Input Voltage versus Output Current

# MUN5111DW1T1 Series

## TYPICAL ELECTRICAL CHARACTERISTICS — MUN5113DW1T1

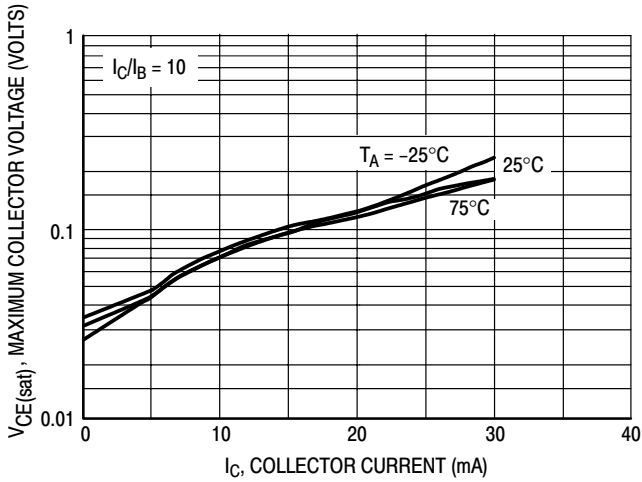


Figure 12.  $V_{CE(sat)}$  versus  $I_C$

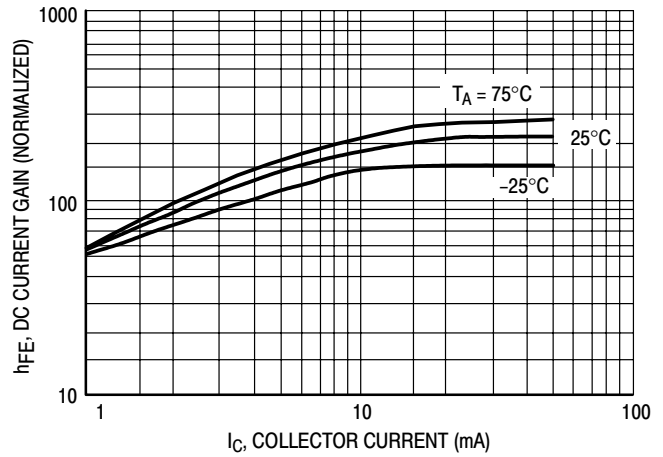


Figure 13. DC Current Gain

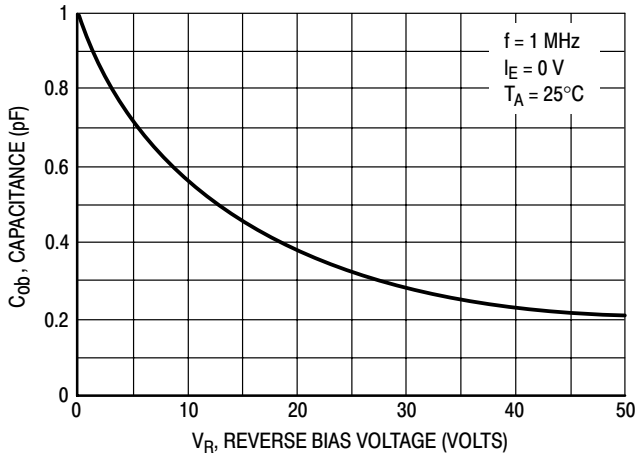


Figure 14. Output Capacitance

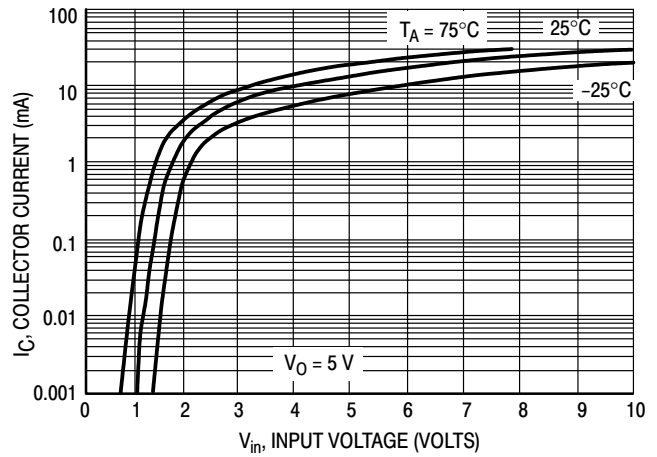


Figure 15. Output Current versus Input Voltage

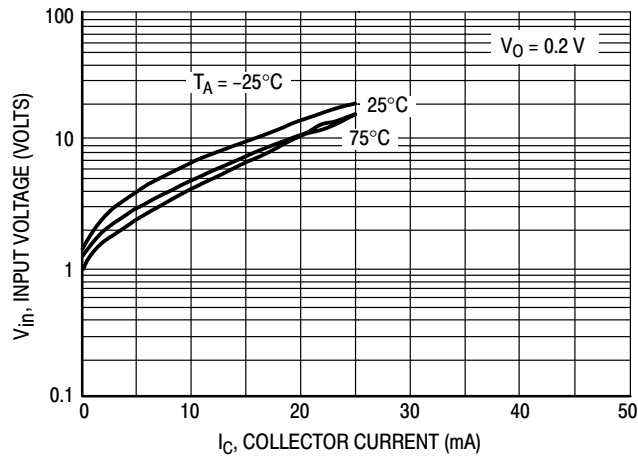


Figure 16. Input Voltage versus Output Current

# MUN5111DW1T1 Series

## TYPICAL ELECTRICAL CHARACTERISTICS — MUN5114DW1T1

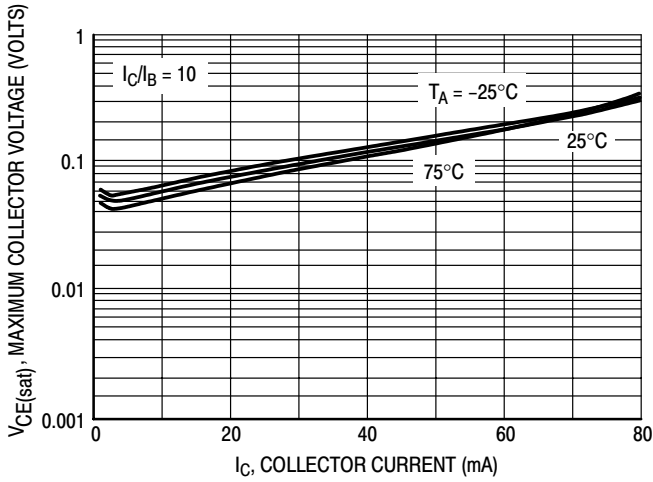


Figure 17.  $V_{CE(sat)}$  versus  $I_C$

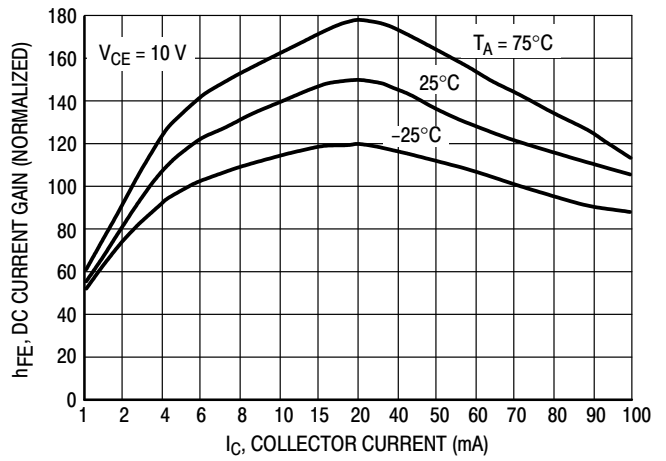


Figure 18. DC Current Gain

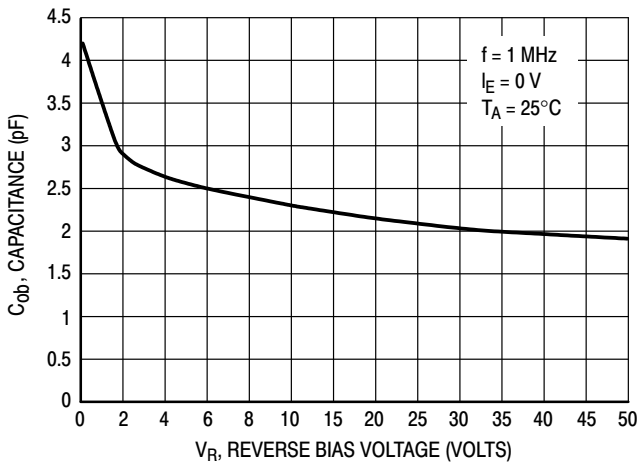


Figure 19. Output Capacitance

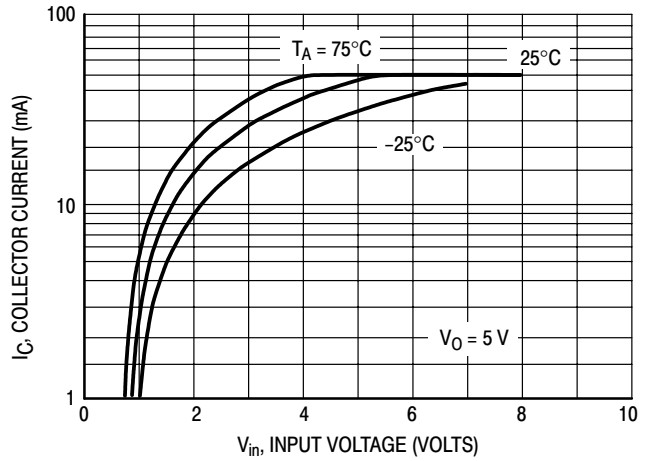


Figure 20. Output Current versus Input Voltage

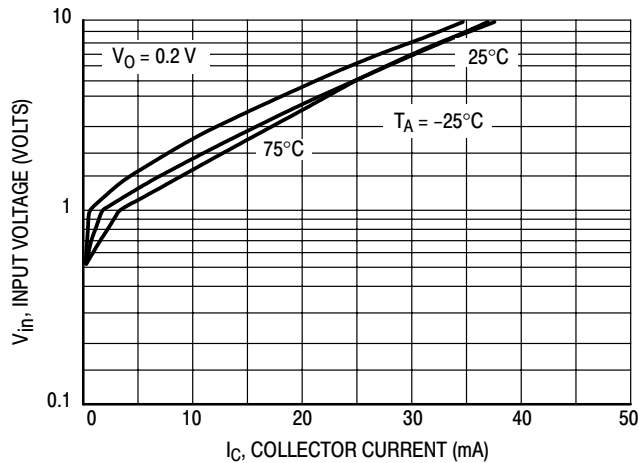


Figure 21. Input Voltage versus Output Current



# MUN5111DW1T1 Series

## TYPICAL ELECTRICAL CHARACTERISTICS — MUN5115DW1T1

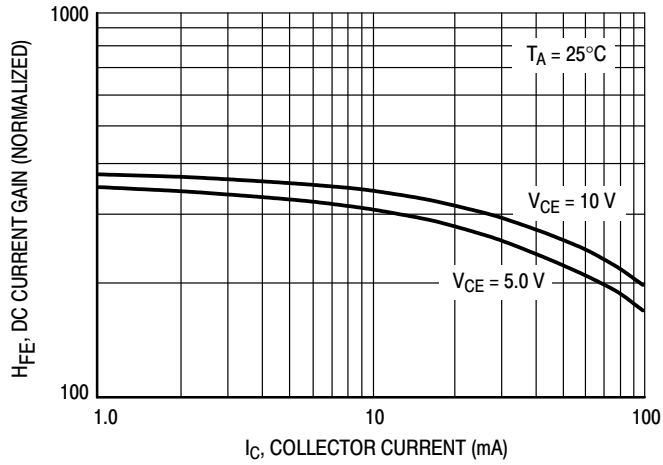


Figure 22. DC Current Gain

## TYPICAL ELECTRICAL CHARACTERISTICS — MUN5116DW1T1

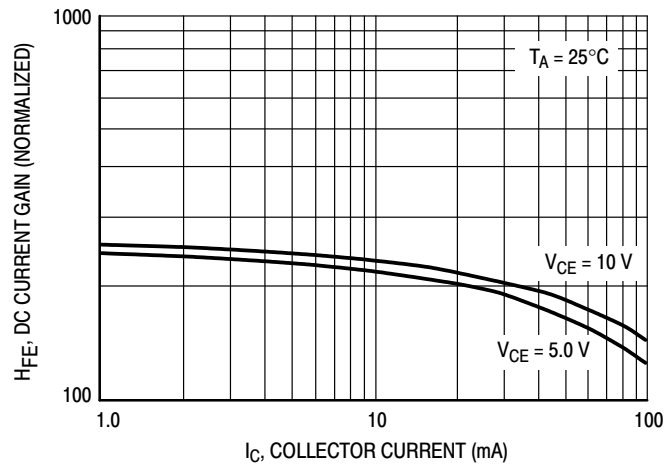
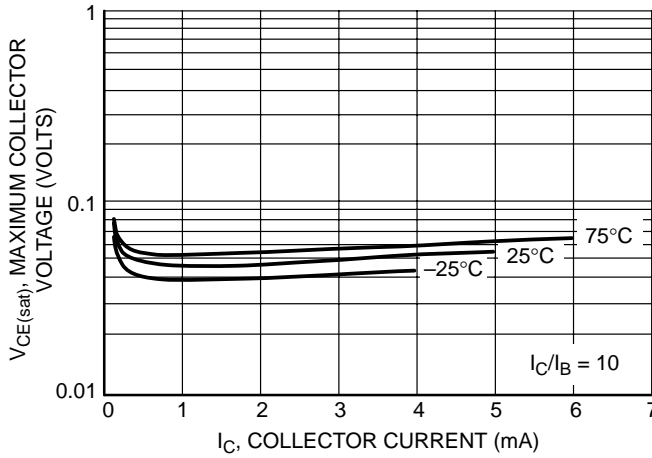


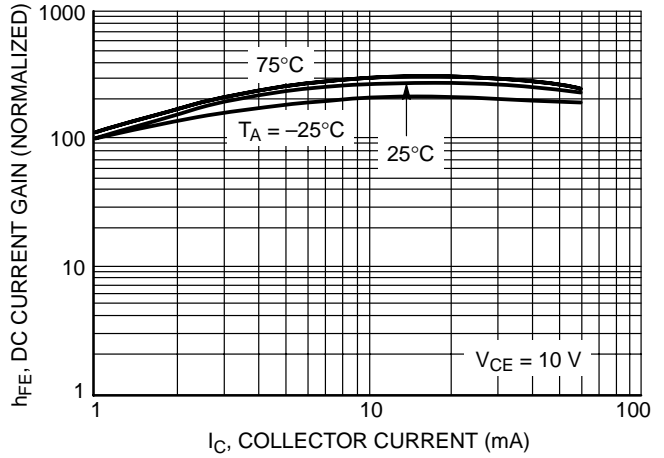
Figure 23. DC Current Gain

# MUN5111DW1T1 Series

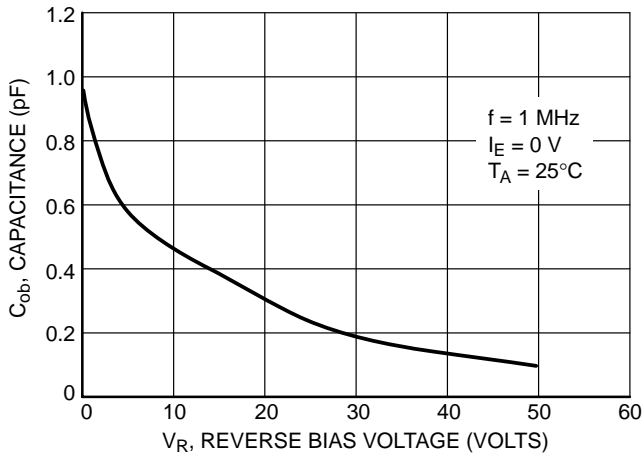
## TYPICAL ELECTRICAL CHARACTERISTICS — MUN5136DW1T1



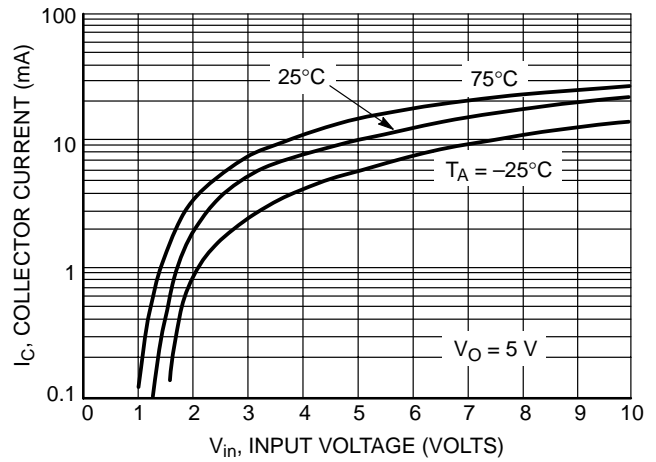
**Figure 24. Maximum Collector Voltage versus Collector Current**



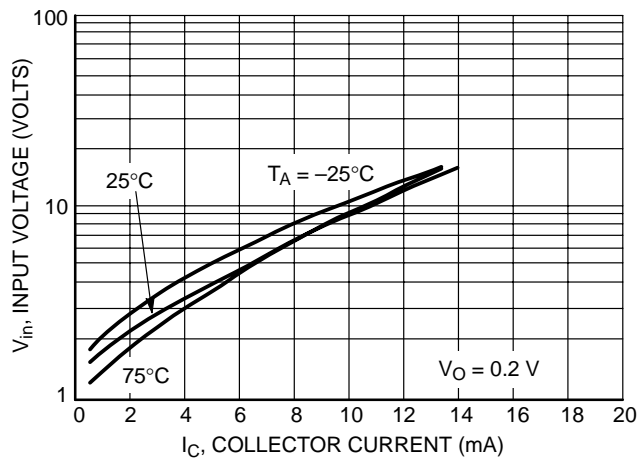
**Figure 25. DC Current Gain**



**Figure 26. Output Capacitance**



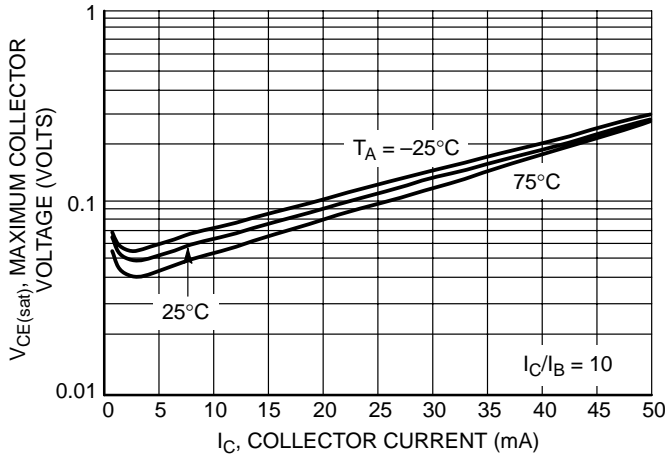
**Figure 27. Output Current versus Input Voltage**



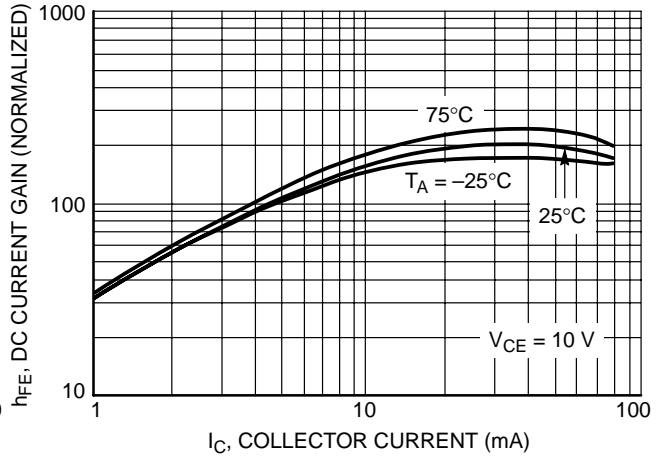
**Figure 28. Input Voltage versus Output Current**

# MUN5111DW1T1 Series

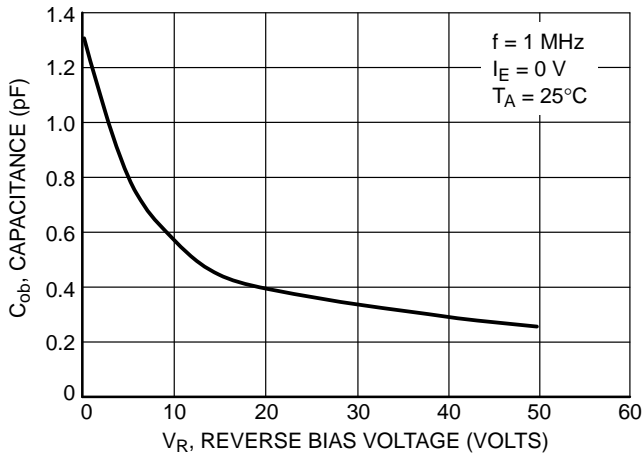
## TYPICAL ELECTRICAL CHARACTERISTICS — MUN5137DW1T1



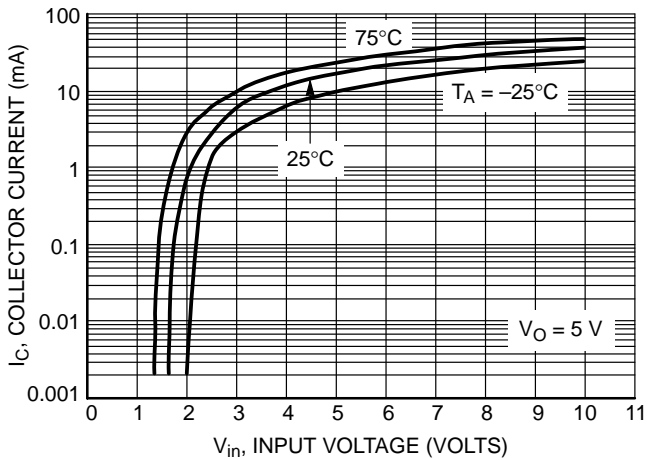
**Figure 29. Maximum Collector Voltage versus Collector Current**



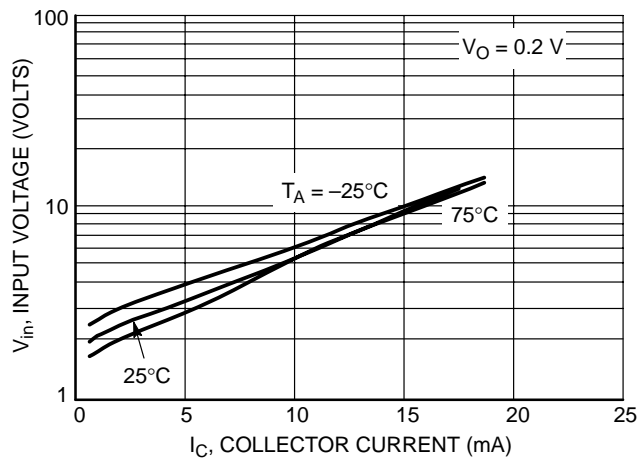
**Figure 30. DC Current Gain**



**Figure 31. Output Capacitance**



**Figure 32. Output Current versus Input Voltage**



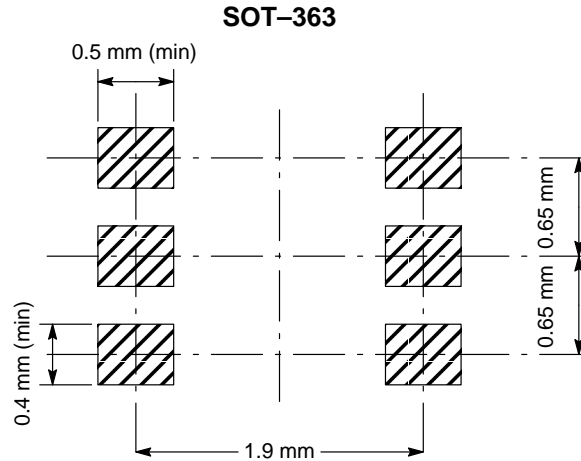
**Figure 33. Input Voltage versus Output Current**

**INFORMATION FOR USING THE SOT-363 SURFACE MOUNT PACKAGE**

**MINIMUM RECOMMENDED FOOTPRINTS FOR SURFACE MOUNTED APPLICATIONS**

Surface mount board layout is a critical portion of the total design. The footprint for the semiconductor packages must be the correct size to insure proper solder connection

interface between the board and the package. With the correct pad geometry, the packages will self align when subjected to a solder reflow process.



**SOT-363 POWER DISSIPATION**

The power dissipation of the SOT-363 is a function of the pad size. This can vary from the minimum pad size for soldering to the pad size given for maximum power dissipation. Power dissipation for a surface mount device is determined by  $T_{J(max)}$ , the maximum rated junction temperature of the die,  $R_{\theta JA}$ , the thermal resistance from the device junction to ambient; and the operating temperature,  $T_A$ . Using the values provided on the data sheet,  $P_D$  can be calculated as follows:

$$P_D = \frac{T_{J(max)} - T_A}{R_{\theta JA}}$$

The values for the equation are found in the maximum ratings table on the data sheet. Substituting these values into the equation for an ambient temperature  $T_A$  of 25°C,

one can calculate the power dissipation of the device which in this case is 256 milliwatts.

$$P_D = \frac{150^\circ\text{C} - 25^\circ\text{C}}{490^\circ\text{C/W}} = 256 \text{ milliwatts}$$

The 490°C/W for the SOT-363 package assumes the use of the recommended footprint on a glass epoxy printed circuit board to achieve a power dissipation of 256 milliwatts. There are other alternatives to achieving higher power dissipation from the SOT-363 package. Another alternative would be to use a ceramic substrate or an aluminum core board such as Thermal Clad™. Using a board material such as Thermal Clad, an aluminum core board, the power dissipation can be doubled using the same footprint.

**SOLDERING PRECAUTIONS**

The melting temperature of solder is higher than the rated temperature of the device. When the entire device is heated to a high temperature, failure to complete soldering within a short time could result in device failure. Therefore, the following items should always be observed in order to minimize the thermal stress to which the devices are subjected.

- Always preheat the device.
- The delta temperature between the preheat and soldering should be 100°C or less.\*
- When preheating and soldering, the temperature of the leads and the case must not exceed the maximum temperature ratings as shown on the data sheet. When using infrared heating with the reflow soldering method, the difference should be a maximum of 10°C.

- The soldering temperature and time should not exceed 260°C for more than 10 seconds.
- When shifting from preheating to soldering, the maximum temperature gradient should be 5°C or less.
- After soldering has been completed, the device should be allowed to cool naturally for at least three minutes. Gradual cooling should be used as the use of forced cooling will increase the temperature gradient and result in latent failure due to mechanical stress.
- Mechanical stress or shock should not be applied during cooling.

\* Soldering a device without preheating can cause excessive thermal shock and stress which can result in damage to the device.

# MUN5111DW1T1 Series

## SOLDER STENCIL GUIDELINES

Prior to placing surface mount components onto a printed circuit board, solder paste must be applied to the pads. A solder stencil is required to screen the optimum amount of solder paste onto the footprint. The stencil is made of brass

or stainless steel with a typical thickness of 0.008 inches. The stencil opening size for the surface mounted package should be the same as the pad size on the printed circuit board, i.e., a 1:1 registration.

## TYPICAL SOLDER HEATING PROFILE

For any given circuit board, there will be a group of control settings that will give the desired heat pattern. The operator must set temperatures for several heating zones, and a figure for belt speed. Taken together, these control settings make up a heating “profile” for that particular circuit board. On machines controlled by a computer, the computer remembers these profiles from one operating session to the next. Figure 34 shows a typical heating profile for use when soldering a surface mount device to a printed circuit board. This profile will vary among soldering systems but it is a good starting point. Factors that can affect the profile include the type of soldering system in use, density and types of components on the board, type of solder used, and the type of board or substrate material being used. This profile shows temperature versus time.

The line on the graph shows the actual temperature that might be experienced on the surface of a test board at or near a central solder joint. The two profiles are based on a high density and a low density board. The Vitronics SMD310 convection/infrared reflow soldering system was used to generate this profile. The type of solder used was 62/36/2 Tin Lead Silver with a melting point between 177–189°C. When this type of furnace is used for solder reflow work, the circuit boards and solder joints tend to heat first. The components on the board are then heated by conduction. The circuit board, because it has a large surface area, absorbs the thermal energy more efficiently, then distributes this energy to the components. Because of this effect, the main body of a component may be up to 30 degrees cooler than the adjacent solder joints.

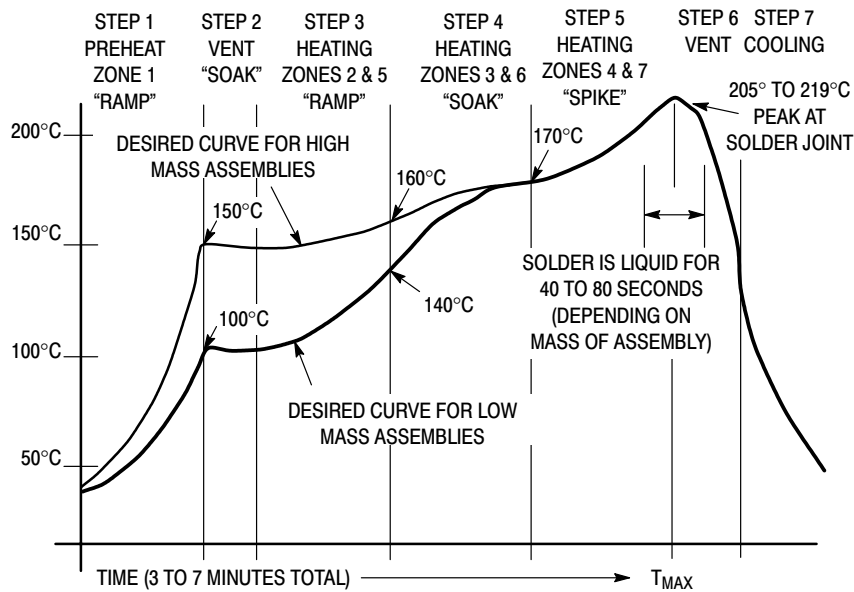
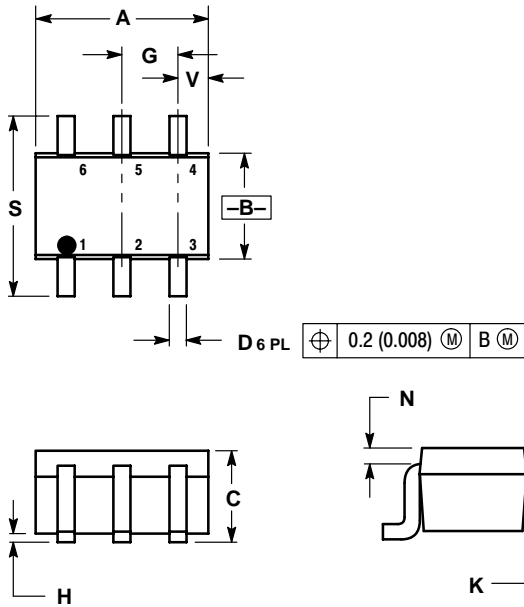


Figure 34. Typical Solder Heating Profile

# MUN5111DW1T1 Series

## PACKAGE DIMENSIONS

SOT-363  
CASE 419B-01  
ISSUE G



- NOTES:  
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20
V	0.012	0.016	0.30	0.40

- STYLE 1:  
PIN 1. EMITTER 2  
2. BASE 2  
3. COLLECTOR 1  
4. EMITTER 1  
5. BASE 1  
6. COLLECTOR 2

**Notes**

# MUN5111DW1T1 Series

Thermal Clad is a trademark of the Bergquist Company

**ON Semiconductor** and  are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

## PUBLICATION ORDERING INFORMATION

### **NORTH AMERICA Literature Fulfillment:**

Literature Distribution Center for ON Semiconductor  
P.O. Box 5163, Denver, Colorado 80217 USA  
**Phone:** 303-675-2175 or 800-344-3860 Toll Free USA/Canada  
**Fax:** 303-675-2176 or 800-344-3867 Toll Free USA/Canada  
**Email:** ONlit@hibbertco.com  
Fax Response Line: 303-675-2167 or 800-344-3810 Toll Free USA/Canada

**N. American Technical Support:** 800-282-9855 Toll Free USA/Canada

**EUROPE:** LDC for ON Semiconductor – European Support

**German Phone:** (+1) 303-308-7140 (Mon-Fri 2:30pm to 7:00pm CET)  
**Email:** ONlit-german@hibbertco.com  
**French Phone:** (+1) 303-308-7141 (Mon-Fri 2:00pm to 7:00pm CET)  
**Email:** ONlit-french@hibbertco.com  
**English Phone:** (+1) 303-308-7142 (Mon-Fri 12:00pm to 5:00pm GMT)  
**Email:** ONlit@hibbertco.com

**EUROPEAN TOLL-FREE ACCESS\*: 00-800-4422-3781**

\*Available from Germany, France, Italy, UK, Ireland

### **CENTRAL/SOUTH AMERICA:**

**Spanish Phone:** 303-308-7143 (Mon-Fri 8:00am to 5:00pm MST)  
**Email:** ONlit-spanish@hibbertco.com  
**Toll-Free from Mexico:** Dial 01-800-288-2872 for Access –  
then Dial 866-297-9322

**ASIA/PACIFIC:** LDC for ON Semiconductor – Asia Support

**Phone:** 303-675-2121 (Tue-Fri 9:00am to 1:00pm, Hong Kong Time)  
**Toll Free from Hong Kong & Singapore:**  
**001-800-4422-3781**

**Email:** ONlit-asia@hibbertco.com

**JAPAN:** ON Semiconductor, Japan Customer Focus Center

4-32-1 Nishi-Gotanda, Shinagawa-ku, Tokyo, Japan 141-0031  
**Phone:** 81-3-5740-2700  
**Email:** r14525@onsemi.com

**ON Semiconductor Website:** <http://onsemi.com>

For additional information, please contact your local Sales Representative.